

High Isolation SPDT Switch DC to 15 GHz Die

ADH232S

1.0 <u>SCOPE</u>

This specification documents the detail requirements for space qualified die per MIL-PRF-38534 class K except as modified herein.

The manufacturing flow described in the SPACE DIE BROCHURE is to be considered a part of this specification.

This datasheet specifically details the space grade version of this product. A more detailed operational description and a complete datasheet for commercial product grades can be found at www.analog.com/HMC232

2.0 <u>Part Number</u>. The complete part number(s) of this specification follow:

Part Number	Description
HMC8800	DC-15GHz High Isolation SPDT Switch Die

3.0 <u>Die Information</u>

3.1 <u>Die Dimensions</u>

Die Size	Die Thickness	Bond Pad and Backside Metalization
41 mil x 81 mil	$4 \text{ mil} \pm 0.5 \text{ mil}$	Au

3.2 Die Picture



Contro	l Input	Signal Pat	th State
Α	В	RFC to RF1	RFC to RF2
High	Low	ON	OFF
Low	High	OFF	ON

Caution: Do not "Hot Switch" power levels greater than +26 dBm (VCTL = 0/-5 VDC)

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Rev. D

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1.	RF1*
2.	A**
3.	B**
4.	RFC*
5.	A**
6.	B**
7.	RF2*
8.	A**
9.	B**

- 10. A**
- Die bottom must be connected to RF ground
- No connection required for unlabeled pads
- * (DC coupled, matched to 50 ohms, blocking cap required if RF line potential not equal to 0V)
- ** Using any one of the A and any one of the B Pads connection is acceptable

One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106, U.S.A. Tel: 781.329.4700 www.analog.com Fax: 781.326.8703 © 2019 Analog Devices, Inc. All rights reserved.

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3.3 Absolute Maximum Ratings 1/

RF Input Power (Vctl = -5V) (0.5 – 15GHz)	+30dBm (@ +50°C)
Control Voltage Range (A & B)	+1 V to -7.5 Vdc
Channel Temperature	150°C
Thermal resistance	92°C/W
Storage Temperature	65°C to +150°C
Operating Temperature	55°C to +85°C
ESD Sensitivity (HBM)	Class 1A

Absolute Maximum Ratings Notes:

1/ Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability.

4.0 <u>Die Qualification</u>

In accordance with class-K version of MIL-PRF-38534, Appendix C, Table C-II, except as modified herein.

- (a) Pre-screen test post assembly required prior to die qualification, to remove all assembly related rejects.
- (b) Mechanical Shock or Constant Acceleration not performed; die qualification is performed in an open carrier.
- (c) Interim and post burn-in electrical tests will include static tests screened at +25°C only.

Table I - Dice Electrical Characteristics						
Parameter	Symbol	Conditions <u>1</u> /, <u>2</u> /, <u>3</u> /, <u>4</u> / 50 Ω System	Limit Min	Limit Max	Units	
Insertion Loss	IL	DC – 6 GHz DC – 10 GHz DC – 15 GHz		1.6 2.2 2.9	dB	
Isolation	lso	DC – 6 GHz DC – 10 GHz DC – 15 GHz	50 45 40		dB	
Return Loss "On State"	S11(on)	DC – 6 GHz DC – 15 GHz	17 9		dB	
Return Loss RF1, RF2 "Off State"	S11(off)	DC – 6 GHz DC – 15 GHz	12 9		dB	
Input Power for 1dB Compression	IP1dB	0.5 – 15 GHz	21		dBm	

Table | Notes:

<u>1/</u> Limits apply at +25°C only.

2/ Tested with VCTLA/B Low = -0.2V, High = -5V

3/ S-par data to be tabulated at 50MHz and every 1GHz, 1GHz to 15GHz. Pin = -25dBm

4/ P1dB shall be measured at 5GHz, 10GHz, 15GHz, Go-No-Go

Table II - Electrical Characteristics for Qualification Samples						
Parameter	Symbol	Conditions <u>1/, 2/, 3/, 4/, 5/, 6/</u> -40C ≤ T _A ≤ 85°C, 50 ohm system unless otherwise specified	Sub- groups	Min Limit	Max Limit	Units
		DC – 6.0 GHz	4		1.6	
			5,6		1.7	
Insertion Loss	IL	DC – 10.0 GHz	4		2.2	dB
			5,6		2.3	
		DC – 15.0 GHz	4		2.9	
			5,6		3.0	
	ISO	DC – 6.0 GHz	4,5,6	55		
Isolation		DC – 10.0 GHz	4,5,6	50		dB
		DC – 15.0 GHz	4,5,6	45		
	RL(on)		4	18		
Return Loss "On State"		DC - 6.0 GH2	5,6	17		dB
		DC – 15.0 GHz	4,5,6	12		
Return Loss RF1, RF2, "Off		DC – 6.0 GHz	4,5,6	14		۵Ŀ
State"	RL(OII)	DC – 15.0 GHz	4,5,6	12		UD
Input Power for 1dB Compression	IP1dB	0.5 – 15.0 GHz	4,5,6	21		dBm
Input Third Order Intercept (Two-Tone P _{IN} = 7 dBm each tone, 1MHz Separation)	IIP3	0.5 – 15.0 GHz	4,5,6	42		dBm

Table II Notes:

Pre burn-in and Post burn-in electrical require S-parameter testing only as defined. Final electrical tests shall incorporate power tests as defined. 1/

Temperature testing required for Final Electrical testing only Tested with VCTLA/B Low = -0.2 V, High = -5 V 2/ 3/ 4/ 5/ 6/

S-par data to be tabulated at 50MHz and every 1 GHz, 1 GHz to 15 GHz. Pin = -25 dBm P1dB shall be measured at 1 GHz to 15 GHz, 2 GHz steps

IP3 shall be measured at 1 GHz to 15GHz, 2 GHz steps

Table III - Endpoint and Delta Limits (+25°C)						
(Product is tested in accordance with Table II with the following exceptions)						
Paramotor	Baramatar Symbol Sub- End-point				Dolta	Units
Falameter	Symbol	groups	Min	Max	Deita	Units

Table III Notes:

1/Table II limits will not be exceeded

 $\frac{1}{2}$ / 240 hour burn in and Group C end point electrical parameters. Deltas are performed at T_A = 25°C

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5.0 <u>Die Outline</u>



NOTES:

- 1. ALL DIMENSIONS IN INCHES [MILLIMETERS]
- 2. BOND PADS ARE 0.004" SQUARE
- 3. TYPICAL BOND PAD SPACING CENTER TO CENTER IS .006"
- 4. BACKSIDE METALIZATION: GOLD
- 5. BOND PAD METALIZATION: GOLD
- 6. BACKSIDE OF DIE IS GROUND
- 7. DIE THICKNESS IS .004"
- 8. NO CONNECTION REQUIRED FOR UNLABLED BOND PADS

- 1. RF1*
- 2. A**
 - 3. B**
 - 4. RFC*
 - 5. A**
 - 6. B**
 - 7. RF2*
 - 8. A**
 - 9. B**
 - 10. A**
 - Die bottom must be connected to RF ground
 - No connection required for unlabeled pads
 - * (DC coupled, matched to 50 ohms, blocking cap required if RF line potential not equal to 0V)
 - ** Using any one of the A and any one of the B Pads connection is acceptable

Rev	Description of Change	Date
А	Initiate	27-October-2015
В	Changes to Section 3.2 (Absolute Maximum Ratings) and added clarification to sections 3.3 and 5.0	12-December- 2015
С	Corrected minimum operating temperature from -40°C to -55°C, and corrected maximum operating temperature from 80°C to 85°C, corrected IP3 test conditions and notes in Table II, corrected numbering in Die Outline pin descriptions	26-February-2018
D	Add note to exceptions list clarifying test temperatures for interim and post burn-in electrical tests	4-June-2019

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